

# BD233/235/237

# Medium Power Linear and Switching Applications

• Complement to BD 234/236/238 respectively



# **NPN Epitaxial Silicon Transistor**

# Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Para	meter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	80	V
V <sub>CER</sub>	Collector-Emitter Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	100	V
$V_{EBO}$	Emitter-Base Voltage		5	V
I <sub>C</sub>	Collector Current (DC)		2	Α
I <sub>CP</sub>	*Collector Current (Pulse)		6	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C	:)	25	W
T <sub>J</sub>	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage					
	: BD233	$I_{C} = 100 \text{mA}, I_{B} = 0$	45			V
	: BD235	_	60			V
	: BD237		80			V
I <sub>CBO</sub>	Collector Cut-off Current					
	: BD233	$V_{CB} = 45V, I_{E} = 0$			100	μΑ
	: BD235	$V_{CB} = 60V, I_{E} = 0$			100	μΑ
	: BD237	$V_{CB} = 100V, I_{E} = 0$			100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 2V, I_{C} = 150 \text{mA}$	40			
		$V_{CE} = 2V, I_{C} = 1A$	25			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.1A$			0.6	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage	$V_{CE} = 2V$ , $I_{C} = 1A$			1.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 250mA$	3			MHz

<sup>\*</sup> Pulse Test: PW=300µs, duty Cycle=1.5% Pulsed

# **Typical Characteristics**

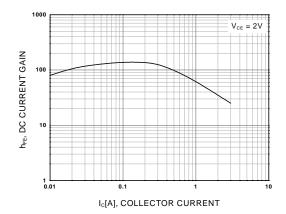


Figure 1. DC current Gain

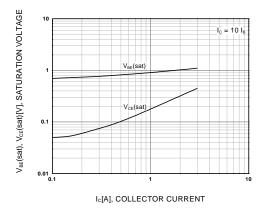


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

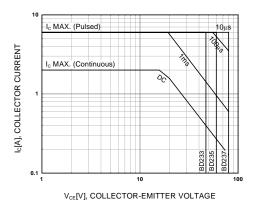


Figure 3. Safe Operating Area

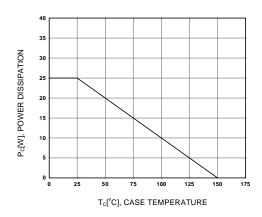
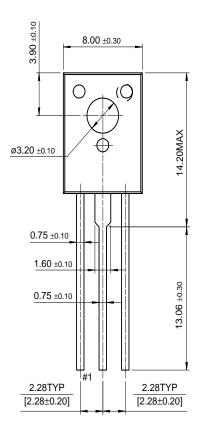
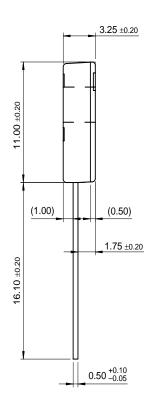


Figure 4. Power Derating

# **Package Demensions**

TO-126







Dimensions in Millimeters

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST <sup>®</sup>	OPTOPLANAR™	STAR*POWER™
Bottomless™	FASTr™	PACMAN™	Stealth™
CoolFET™	FRFET™	POP™	SuperSOT™-3
$CROSSVOLT^{rM}$	GlobalOptoisolator™	Power247™	SuperSOT™-6
DenseTrench™	GTO™	PowerTrench <sup>®</sup>	SuperSOT™-8
DOME™	HiSeC™	QFET™	SyncFET™
EcoSPARK™	ISOPLANAR™	QS™	TruTranslation™
E <sup>2</sup> CMOS™	LittleFET™	QT Optoelectronics™	TinyLogic™
EnSigna™	MicroFET™	Quiet Series™	UHC™
FACT™	MICROWIRE™	SLIENT SWITCHER®	UltraFET <sup>®</sup>
FACT Quiet Series™	OPTOLOGIC™	SMART START™	VCX™

STAR\*POWER is used under license

#### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### **LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

©2001 Fairchild Semiconductor Corporation Rev. H

# AMEYA360 Components Supply Platform

# **Authorized Distribution Brand:**

























## Website:

Welcome to visit www.ameya360.com

## Contact Us:

## > Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

## > Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

## Customer Service :

Email service@ameya360.com

# Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com